

Revision 0.90

SINGLE FREQUENCY LASER DIODES Distributed Feedback Laser



General Product Information

Product	Application
780 nm DFB Laser	Spectroscopy (Rb D2 line)
with hermetic 14-Pin Butterfly Housing (RoHS compliant)	Metrology
including Monitor Diode, Thermoelectric Cooler and Thermistor	THz Generation
with integrated Beam Collimation	



Absolute Maximum Ratings

Parameter	Symbol	Unit	min	typ	max
Storage Temperature	T _S	°C	-40		85
Operational Temperature at Case	T_{C}	°C	-40		85
Operational Temperature at Laser Chip	T_LD	°C	10		50
Forward Current	I _F	mA			190
Reverse Voltage	V_R	V			2
Output Power	P_{opt}	mW			90
TEC Current	I_{TEC}	Α			1.1
TEC Voltage	V_{TEC}	V			2.8

Measurement Conditions / Comments

Stress in excess of one of the Absolute Maximum Ratings may damage the laser. Please note that a damaging optical power level may occur although the maximum current is not reached. These are stress ratings only, and functional operation at these or any other conditions beyond those indicated under Recommended Operational Conditions is not implied.

Recommended Operational Conditions

Parameter	Symbol	Unit	min	typ	max
Operational Temperature at Case	T_{case}	°C	-20		65
Operational Temperature at Laser Chip	T_LD	°C	15		45
Forward Current	I _F	mA			180
Output Power	P_{opt}	mW	20		80

Measurement Conditions / Comments			
measured by integrated Thermistor			

Characteristics at $T_{LD} = 25^{\circ}$ at BOL

Parameter	Symbol	Unit	min	typ	max
Center Wavelength	λ_{C}	nm	779	780	781
Target Wavelength	λ_{T}	nm		780.24	
Linewidth (FWHM)	Δλ	MHz		0.6	1
Mode-hop free Tuning Range	$\Delta \lambda_{\text{tune}}$	pm	25		
Sidemode Supression Ratio	SMSR	dB	30	50	
Temperature Coefficient of Wavelength	dλ / dT	nm / K		0.06	
Current Coefficient of Wavelength	dλ / dl	nm / mA		0.003	

Measure	ment Conditions / Comments

see images on page 4
reached within T _{LD} = 15 ° 45° C at 80 mW
> 10 GHz, at target wavelength
$P_{opt} = 80 \text{ mW}$

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Characteristics at T _{LD} =	: 25° at B	OL			cont'd
Parameter	Symbol	Unit	min	typ	max
Laser Current @ P _{opt} = 80 mW	I _{LD}	mA			180
Slope Efficiency	η	W/A	0.6	0.8	1.0
Threshold Current	I_{th}	mA			70
Divergence parallel (FWHM)	$\Theta_{ }$	0		0.1	
Divergence perpendicular (FWHM)	Θ_{\perp}	0		0.1	
Beam Diameter horizontal	d	mm		1.0	1.2
Beam Diameter vertical	d_\perp	mm		0.8	1.2
Degree of Polarization	DOP	%		90	

parallel to the base plate of the housing (see p. 3)
perpendicular to base plate of the housing (see p. 3)
parallel to the base plate of the housing (see p. 3)
perpendicular to base plate of the housing (see p. 3)
$P_{\rm opt} = 80$ mW; E field perpendicular to the base plate

Measurement Conditions / Comments

Monitor Diode					
Parameter	Symbol	Unit	min	typ	max
Monitor Detector Responsivity	I _{mon} / P _{opt}	μΑ/mW	1		20

Measi	urement Conditions / Comments
$J_R =$	5 V

I nermoelectric Cooler					
Parameter	Symbol	Unit	min	typ	max
Current	I _{TEC}	А		0.4	
Voltage	U_TEC	V		1.3	
Power Dissipation (total loss at case)	P _{loss}	W		0.5	
Temperature Difference	ΔΤ	K			50

Measurement Conditions / Comments						

Parameter	Symbol	Unit	min	typ	max
Resistance	R	kΩ		10	
Beta Coefficient	β			3892	
Steinhart & Hart Coefficient A	А			1.1293 x 10	-3
Steinhart & Hart Coefficient B	В		2.3410 x 10 ⁻⁴		
Steinhart & Hart Coefficient C	C		;	3.7755 x 10	-8

Thermistor (Standard NTC Type)

Measurement Conditions / Comments					
$T_{LD} = 25^{\circ} C$					
$R_1/R_2 = e^{\beta(1/T_1-1/T_2)}$ at $T_{LD} =$	0° 50° C				
$1/T = A + B(\ln R) + C(\ln R)^3$					
T: temperature in Kelvin					
R: resistance at T in Ohm					



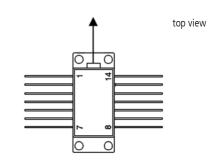
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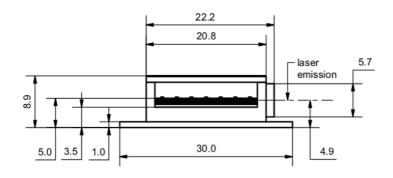


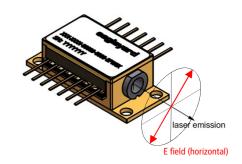
Pin Assignment

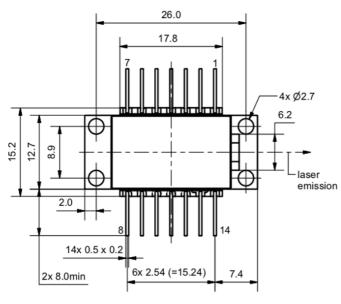
1	Thermoelectric Cooler (+)	14	Thermoelectric Cooler (-)			
2	Thermistor	13	Case			
3	Photodiode (Anode)	12	not connected			
4	Photodiode (Cathode)	11	Laser Diode (Cathode)			
5	Thermistor	10	Laser Diode (Anode)			
6	not connected	9	not connected			
7	not connected	8	not connected			
All 14 pins are isolated from case.						



Package Drawings







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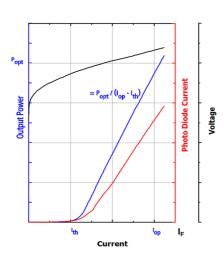
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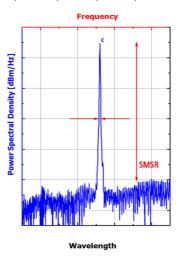


Typical Measurement Results

Output Power vs. Current



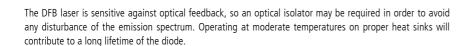
Spectra at Specified Optical Output Power



Performance figures, data and any illustrative material provided in this specification are typical and must be specifically confirmed in writing by eagleyard Photonics before they become applicable to any particular order or contract. In accordance with the eagleyard Photonics policy of continuous improvement specifications may change without notice.

Unpacking, Installation and Laser Safety

Unpacking the laser diodes should only be done at electrostatic safe workstations (EPA). Though protection against electro static discharge (ESD) is implemented in the laser package, charges may occur at surfaces. Please store this product in its original package at a dry, clean place until final use. During device installation, ESD protection has to be maintained.



Avoid direct and/or indirect exposure to the free running beam. Collimating and focussing the free running beam with optics as common in optical instruments will increase threat to the human eye.

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Laser Emission



INVISIBLE LASER RADIATION
AVOID EVE OR SKIN EXPOSURE
TO DIRECT OR SCATTERED RADIATION
CLASS 4 LASER PRODUCT
WAVELENGTH 780 nm
MAX. OUTPUT POWER 90 mW





